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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/076,055	02/14/2002	Teruo Takizawa	9319S-000329	8662
27572 7590 10/01/2004				INER
HARNESS, I	DICKEY & PIERCE,	TRAN, THIEN F		
P.O. BOX 828 BLOOMFIELD HILLS, MI 48303			ART UNIT	PAPER NUMBER
220 cm 1322 11223, 112			2811	
			DATE MAILED: 10/01/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
Office Action Summany	10/076,055	TAKIZAWA, TERUO				
Office Action Summary	Examiner	Art Unit				
	Thien F Tran	2811				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1: after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period v - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be tim y within the statutory minimum of thirty (30) days vill apply and will expire SIX (6) MONTHS from i cause the application to become ABANDONET	ely filed will be considered timely. the mailing date of this communication. (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on 19 Ju	Responsive to communication(s) filed on 19 July 2004.					
2a)⊠ This action is FINAL. 2b)☐ This	This action is FINAL. 2b) ☐ This action is non-final.					
3) Since this application is in condition for allowar	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
closed in accordance with the practice under E	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims						
4)⊠ Claim(s) <u>1,3,4 and 9</u> is/are pending in the application.						
	4a) Of the above claim(s) is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.	b)					
6)⊠ Claim(s) <u>1,3,4 and 9</u> is/are rejected.						
·	Claim(s) is/are objected to.					
8) Claim(s) are subject to restriction and/o	r election requirement.					
Application Papers						
9) The specification is objected to by the Examiner.						
) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correct						
11)☐ The oath or declaration is objected to by the Ex	aminer. Note the attached Office	Action or form P1O-152.				
Priority under 35 U.S.C. § 119						
12) ☐ Acknowledgment is made of a claim for foreign a) ☐ All b) ☐ Some * c) ☐ None of:		-(d) or (f).				
1. Certified copies of the priority documents have been received.						
 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage 						
application from the International Bureau	•	d in this National Stage				
* See the attached detailed Office action for a list	, , , , , , , , , , , , , , , , , , , ,	d				
Coo the attached detailed office determined a list	2. 2.0 Columba Copied Het 1000140					
Attachment(s)						
1) Notice of References Cited (PTO-892)	4) Interview Summary	(PTO-413)				
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Da	te				
 Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 	5) Notice of Informal Pa	atent Application (PTO-152)				

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DETAILED ACTION

Claim Objections

Claim 9 is objected to because of the following informalities: line 7, "drain region" should be --source region--. Appropriate correction is required.

Claim Rejections - 35 USC § 112

The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

Claim 9 is rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. The thickness of the semiconductor film 107 less than 50 nm is not disclosed and shown in the specification, therefore, the recitation of the thickness of the semiconductor film 107 less than 50 nm is not supported by the disclosure. In fact, page 9 paragraph [0049] of the specification discloses the Si film 107 with a thickness Xt of 50 nm. Applicant is requested to point out exactly wherein the application that discloses the thickness of the semiconductor film 107 could be less than 50 nm.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

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A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

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Claims 1, 3 and 4 are rejected under 35 U.S.C. 102(e) as being anticipated by Adan (USPN 6,288,425).

Adan discloses the claimed semiconductor device (Fig. 1) comprising a field effect transistor formed on a SOI substrate, the semiconductor device characterized in comprising a gate region 4 formed on a semiconductor film 3 of the SOI substrate; source and drain regions13b each spaced a specified distance from a channel region 5 formed in the semiconductor film below the gate region, each of the source and drain regions 13 being a first conductive type (n-type); a first extension region 13a that extends from the source region to the channel region; and a second extension region 13a that extends from the drain region to the channel region, wherein junction depths of the first and second extension regions 13a are 50% or less of the junction depth of each of the source region and the drain region 13b, and the channel region 5 between the first and second extension regions 13a being a second conductive type (p-type).

Regarding claim 3, the device is operating in a fully depleted operation mode (col. 3, lines 59-63).

Regarding claim 4, the SOI substrate is a substrate composed of a glass, quartz substrate and a semiconductor film formed thereon (col. 3, lines 36-40).

Response to Arguments

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Applicant's arguments with respect to claims 1, 3, 4 and 9 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thien F Tran whose telephone number is (571) 272-1665. The examiner can normally be reached on 8:30AM - 5:00PM Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C Lee can be reached on (571) 272-1732. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

tt September 27, 2004

THIENTRAN
PRIMARY EXAMINER